

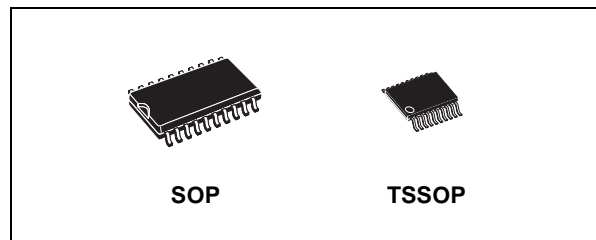


74LVC541A

OCTAL D-TYPE LATCH HIGH PERFORMANCE

PRELIMINARY DATA

- 5V TOLERANT INPUTS
- HIGH SPEED: $t_{PD} = 4.2ns$ (MAX.) at $V_{CC} = 3V$
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24mA$ (MIN) at $V_{CC} = 3V$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 1.65V$ to $3.6V$ (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 541
- LATCH-UP PERFORMANCE EXCEEDS 500mA (JESD 17)
- ESD PERFORMANCE:
HBM > 2000V (MIL STD 883 method 3015);
MM > 200V



ORDER CODES

PACKAGE	TUBE	T & R
SOP	74LVC541AM	74LVC541AMTR
TSSOP		74LVC541ATTR

DESCRIPTION

The 74LVC541A is a low voltage CMOS OCTAL BUS BUFFER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for 1.65 to 3.6 V_{CC} operations and low power and low noise applications.

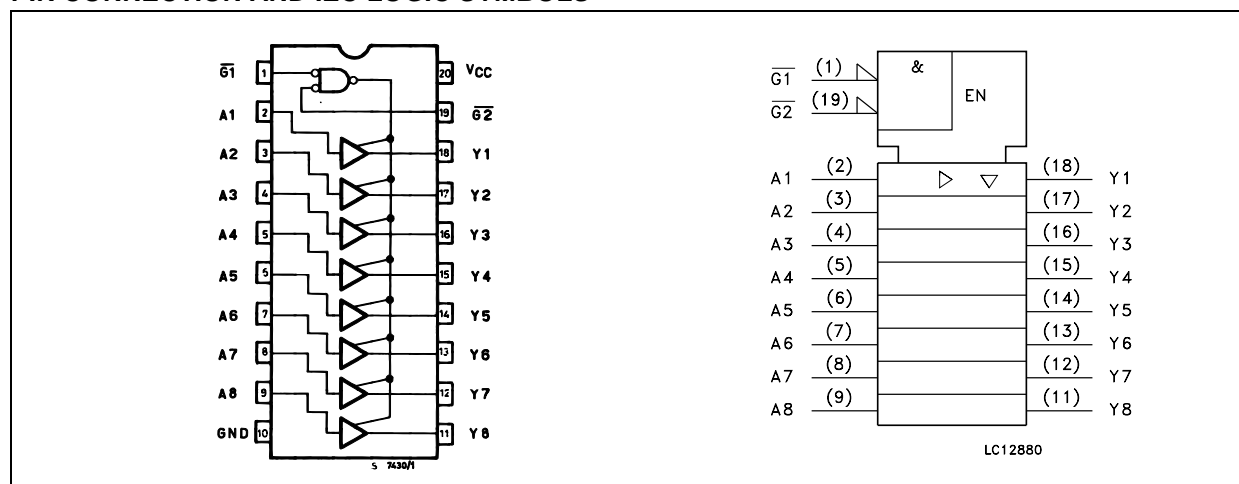
The 3 STATE control gate operates as two input AND such that if either G1 or G2 are high, all eight outputs are in the high impedance state.

In order to enhance PC board layout, the 74LVC541A offers a pinout having inputs and outputs on opposite sides of the package. This device is designed to interface directly High Speed CMOS systems with TTL and NMOS components.

It has more speed performance at 3.3V than 5V AC/ACT family, combined with a lower power consumption.

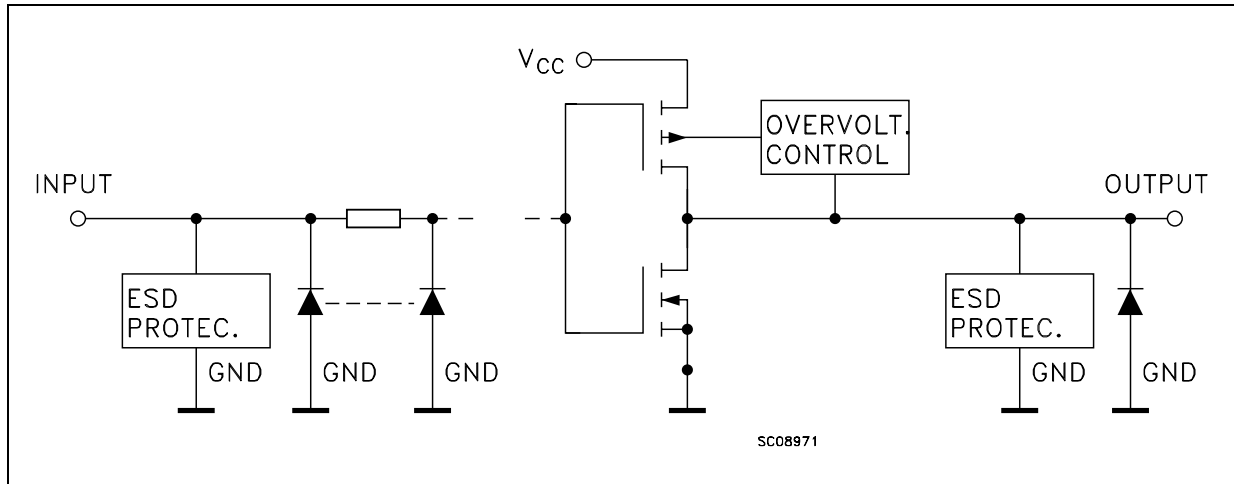
All inputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



74LVC541A

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 19	G1, G2	Output Enable Inputs
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	Y1 to Y8	Data Outputs
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

TRUTH TABLE

INPUT			OUTPUT
$\overline{G1}$	$\overline{G2}$	A _n	Y _n
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

X=Don't care; Z=High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter ²	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage (V _{CC} = 0V)	-0.5 to +7.0	V
V _O	DC Output Voltage (High or Low State) (note 1)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note 2)	- 50	mA
I _O	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current per Supply Pin	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Rating are those value beyond which damage to the device may occur. Functional operation under these condition is not implied

1) I_O absolute maximum rating must be observed

2) V_O < GND, V_O > V_{CC}

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	1.65 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage ($V_{CC} = 0V$)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to $3.6V$)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.7$ to $3.0V$)	± 12	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.3$ to $2.7V$)	± 8	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 1.65$ to $2.3V$)	± 4	mA
T_{op}	Operating Temperature	-40 to 85	$^{\circ}C$
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

2) V_{IN} from 0.8V to 2V at $V_{CC} = 3.0V$

DC SPECIFICATION

Symbol	Parameter	Test Condition		Value				Unit
		V_{CC} (V)		-40 to 85 $^{\circ}C$		-55 to 125 $^{\circ}C$		
				Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	1.65 to 1.95		$0.65V_{CC}$		$0.65V_{CC}$		V
		2.3 to 2.7		1.7		1.7		
		2.7 to 3.6		2		2		
V_{IL}	Low Level Input Voltage	1.65 to 1.95			$0.35V_{CC}$		$0.35V_{CC}$	V
		2.3 to 2.7			0.7		0.7	
		2.7 to 3.6			0.8		0.8	
V_{OH}	High Level Output Voltage	1.65 to 3.6	$I_O = -100 \mu A$	$V_{CC} - 0.2$		$V_{CC} - 0.2$		V
		1.65	$I_O = -4 \text{ mA}$	1.2		1.2		
		2.3	$I_O = -8 \text{ mA}$	1.7		1.7		
		2.7	$I_O = -12 \text{ mA}$	2.2		2.2		
		3.0	$I_O = -18 \text{ mA}$	2.4		2.4		
V_{OL}	Low Level Output Voltage	1.65 to 3.6	$I_O = 100 \mu A$		0.2		0.2	V
		1.65	$I_O = 4 \text{ mA}$		0.45		0.45	
		2.3	$I_O = 8 \text{ mA}$		0.7		0.7	
		2.7	$I_O = 12 \text{ mA}$		0.4		0.4	
		3.0	$I_O = 24 \text{ mA}$		0.55		0.55	
I_I	Input Leakage Current	3.6	$V_I = 0$ to $5.5V$		± 5		± 5	μA
I_{off}	Power Off Leakage Current	0	V_I or $V_O = 5.5V$		100		100	μA
I_{OZ}	High Impedance Output Leakage Current	3.6	$V_I = V_{IH}$ or V_{IL} $V_O = 0$ to $5.5V$		± 5		± 5	μA
I_{CC}	Quiescent Supply Current	3.6	$V_I = V_{CC}$ or GND		10		10	μA
			V_I or $V_O = 3.6$ to $5.5V$		± 10		± 10	
ΔI_{CC}	I_{CC} incr. per Input	2.7 to 3.6	$V_{IH} = V_{CC} - 0.6V$		500		500	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
V _{OLP} V _{OLV}	Dynamic Low Level Quiet Output (note 1)	3.3	C _L = 50pF V _{IL} = 0V, V _{IH} = 3.3V		0.8 -0.8		V

1) Number of output defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining outputs is measured in the LOW state.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition				Value				Unit
		V _{CC} (V)	C _L (pF)	R _L (Ω)	t _s = t _r (ns)	-40 to 85 °C		-55 to 125 °C		
						Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time	1.65 to 1.95	30	1000	2.0					ns
		2.3 to 2.7	30	500	2.0					
		2.7	50	500	2.5	1.5		1.5		
		3.0 to 3.6	50	500	2.5	1		1		
t _{PZL} t _{PZH}	Output Enable Time	1.65 to 1.95	30	1000	2.0					ns
		2.3 to 2.7	30	500	2.0					
		2.7	50	500	2.5	1		1		
		3.0 to 3.6	50	500	2.5	1		1		
t _{PLZ} t _{PHZ}	Output Disable Time	1.65 to 1.95	30	1000	2.0					ns
		2.3 to 2.7	30	500	2.0					
		2.7	50	500	2.5	2		2		
		3.0 to 3.6	50	500	2.5	2		2		
t _{OSLH} t _{OSHL}	Output To Output Skew Time (note 1, 2)	2.7 to 3.6					1		1	ns

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW (t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)

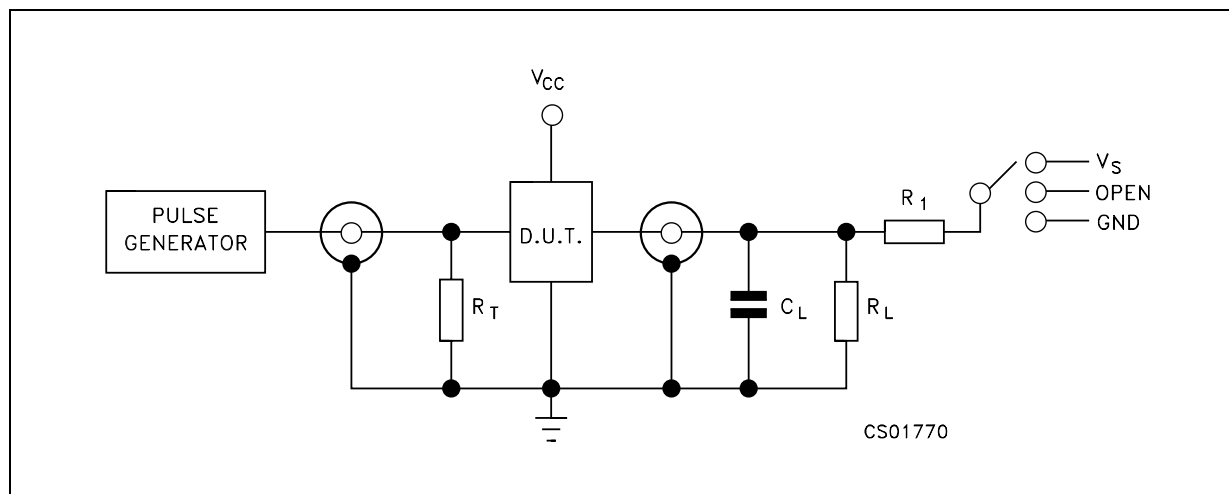
2) Parameter guaranteed by design

CAPACITANCE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
C _{IN}	Input Capacitance				4		pF
C _{PD}	Power Dissipation Capacitance (note 1)	1.8	f _{IN} = 10MHz		28		pF
		2.5			30		
		3.3			34		

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average current can be obtained by the following equation. I_{CC(opr)} = C_{PD} × V_{CC} × f_{IN} + I_{CC}/n (per circuit)

TEST CIRCUIT

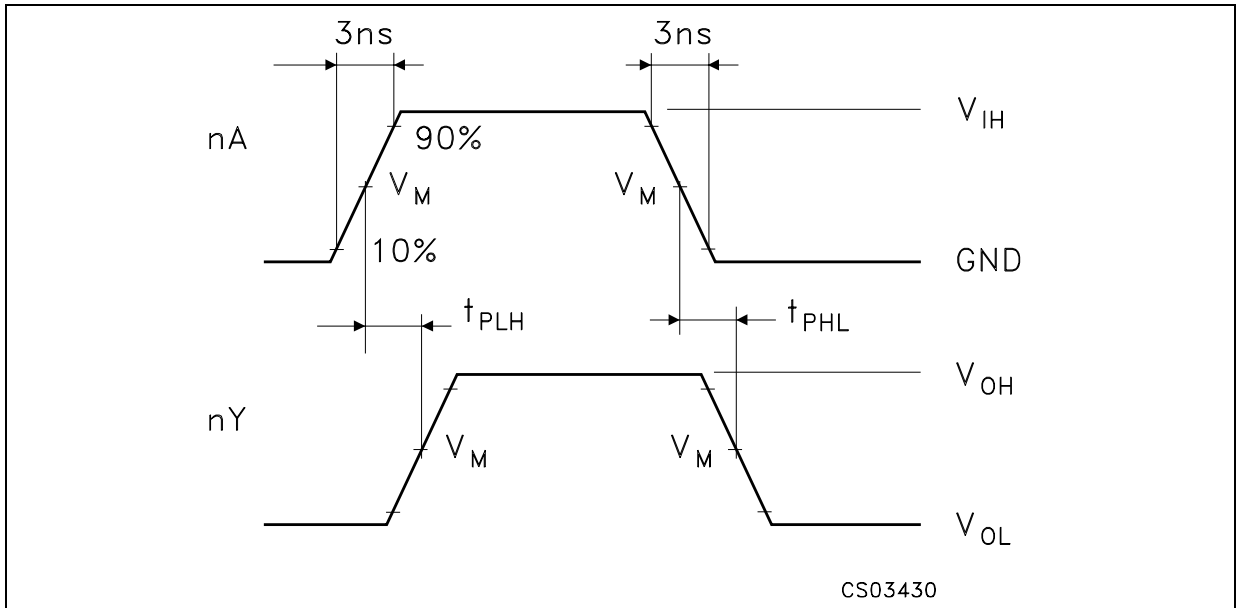


$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

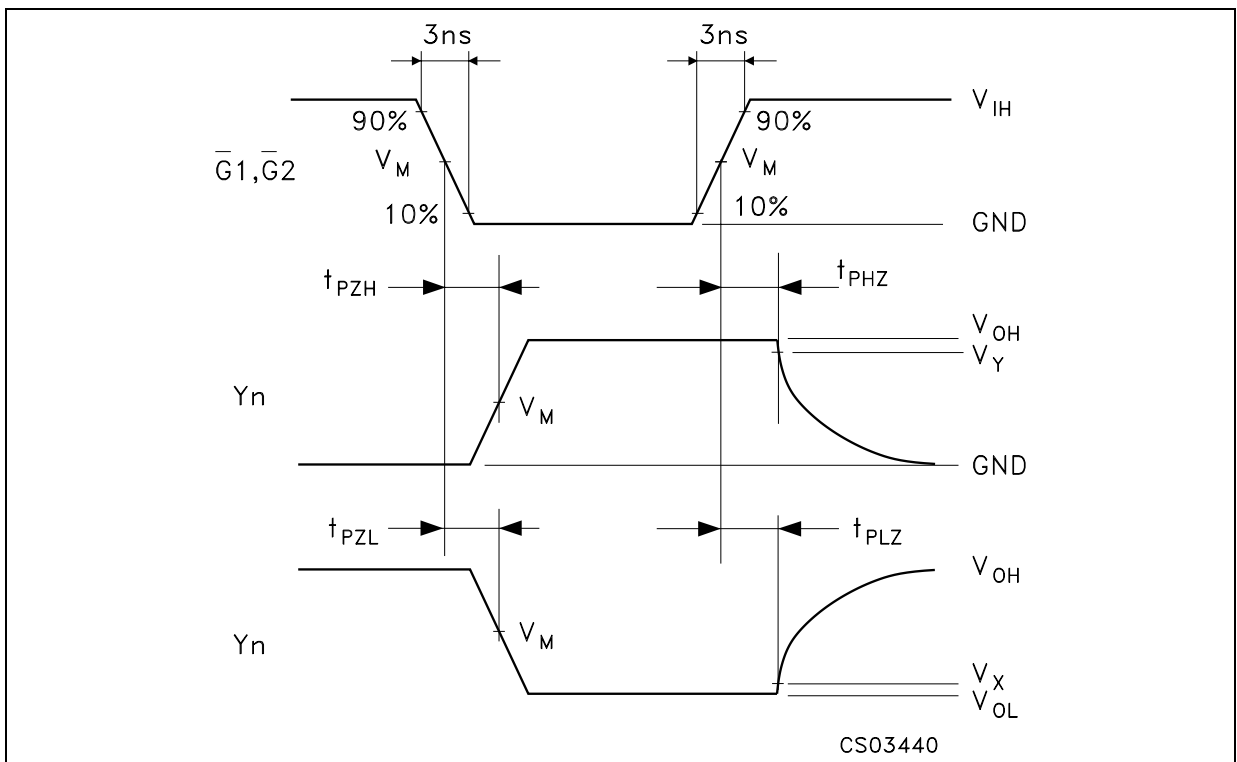
TEST CIRCUIT AND WAVEFORM SYMBOL VALUE

Symbol	V_{CC}			
	1.65 to 1.95V	2.3 to 2.7V	2.7V	3.0 to 3.6V
C_L	30pF	30pF	50pF	50pF
$R_L = R_1$	1000 Ω	500 Ω	500 Ω	500 Ω
V_S	$2 \times V_{CC}$	$2 \times V_{CC}$	6V	7V
V_{IH}	V_{CC}	V_{CC}	2.7V	3.0V
V_M	$V_{CC}/2$	$V_{CC}/2$	1.5V	1.5V
V_{OH}	V_{CC}	V_{CC}	3.0V	3.5V
V_X	$V_{OL} + 0.15V$	$V_{OL} + 0.15V$	$V_{OL} + 0.3V$	$V_{OL} + 0.3V$
V_Y	$V_{OH} - 0.15V$	$V_{OH} - 0.15V$	$V_{OH} - 0.3V$	$V_{OH} - 0.3V$
$t_r = t_f$	<2.0ns	<2.0ns	<2.5ns	<2.5ns

WAVEFORM 1: PROPAGATION DELAYS, (f=1MHz; 50% duty cycle)



WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES (f=1MHz; 50% duty cycle)



SO-20 MECHANICAL DATA

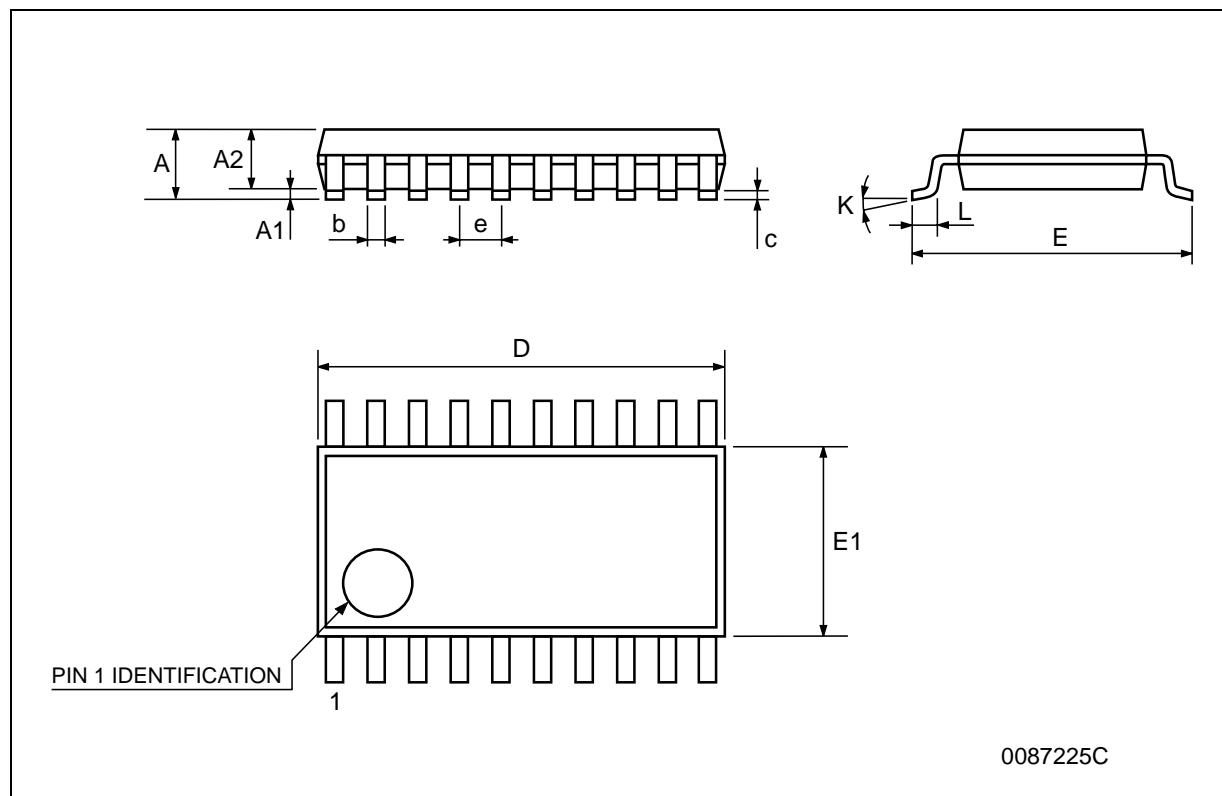
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



PO13L

TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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